PBSS5540X 40 V, 5 A PNP low VCEsat (BISS) transistor 20 March 2018

Product data sheet

1. General description

PNP low V_{CEsat} transistor in a medium power SOT89 (SC-62) package.

NPN complement: PBSS4540X.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High efficiency leading to less heat generation.
- AEC-Q101 qualified

3. Applications

- Supply line switching circuits
- Battery management applications
- DC/DC converter applications
- Strobe flash units
- Medium power driver (e.g. relays, buzzers and motors).

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-40	V
I _C	collector current		-	-	-4	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-10	Α
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -0.5 A; T_{amb} = 25 °C	250	-	-	
R _{CEsat}	collector-emitter saturation resistance	I_C = -5 A; I_B = -500 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	45	75	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		C
2	С	collector		В—
3	В	base	3 2 1 SOT89	E sym132

6. Ordering information

Table 3. Ordering information

Type number		Package					
		Name	Description	Version			
	PBSS5540X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS5540X	%1G

[1] % = placeholder for manufacturing site code

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8. Limiting values

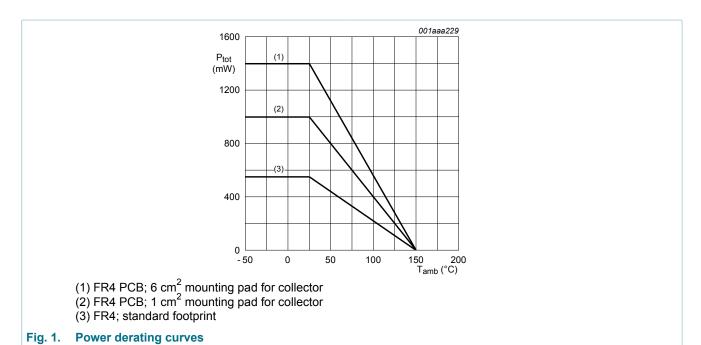
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-40	V
V _{CEO}	collector-emitter voltage	open base		-	-40	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-4	Α
I _{CRM}	repetitive peak collector current	$\delta \le 0.2 \; ; t_p \le 10 \; \text{ms}$		-	-5	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-10	Α
I _B	base current			-	-1	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-2	Α
P _{tot}	total power dissipation		[1] [2]	-	2.5	W
		T _{amb} ≤ 25 °C	[2]	-	0.55	W
			[3]	-	1	W
			[4]	-	1.4	W
			<u>[5]</u>	-	1.6	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Pulsed $t_p \le 10$ ms; $\delta \le 0.2$ Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [2]
- [3] [4]
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a 7 cm² ceramic printed-circuit board, 1 cm² single-sided copper and tin-plated.

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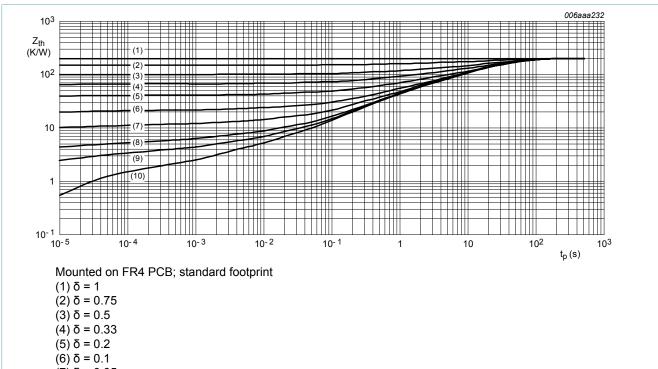
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9. Thermal characteristics

Table 6. Thermal characteristics

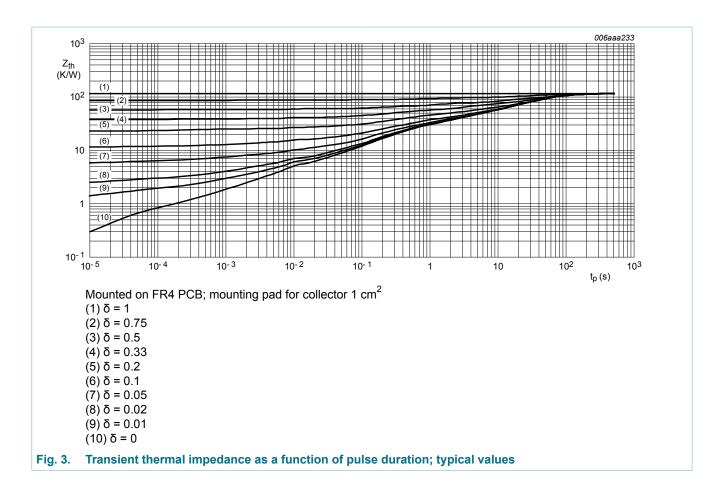
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	1	[1] [2]	-	-	50	K/W
	from junction to ambient		[1]	-	-	225	K/W
			[3]	-	-	125	K/W
			[4]	-	-	90	K/W
			[5]	-	-	80	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	16	K/W

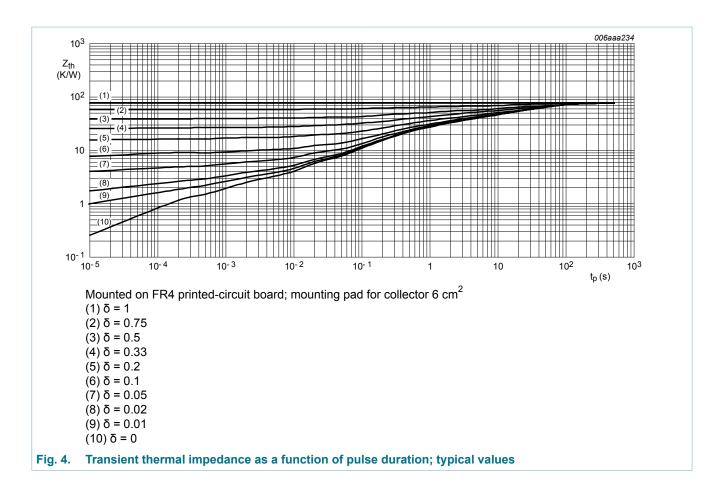
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Pulse test: $t_0 \le 10 \text{ ms}$; $\delta \le 0.2$.
- [3]
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a 7 cm² ceramic printed-circuit board, 1 cm² single-sided copper and tin-plated.



- $(7) \delta = 0.05$
- $(8) \delta = 0.02$
- $(9) \delta = 0.01$
- $(10) \delta = 0$

Transient thermal impedance as a function of pulse duration; typical values Fig. 2.





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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -0.5 A; T_{amb} = 25 °C	250	-	-	
		V_{CE} = -2 V; I_{C} = -1 A; t_{p} ≤ 300 μs; pulsed; δ ≤ 0.02 ; T_{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -2 A; t_{p} ≤ 300 μs; pulsed; δ ≤ 0.02 ; T_{amb} = 25 °C	150	-	-	
		V_{CE} = -2 V; I_{C} = -5 A; t_{p} ≤ 300 μs; pulsed; δ ≤ 0.02 ; T_{amb} = 25 °C	50	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -0.5 \text{ A}; I_B = -5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-120	mV
		I_C = -1 A; I_B = -10 mA; T_{amb} = 25 °C	-	-	-170	mV
		I_C = -2 A; I_B = -200 mA; T_{amb} = 25 °C	-	-	-160	mV
		I_C = -4 A; I_B = -200 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	-340	mV
		I_C = -5 A; I_B = -500 mA; $t_p \le 300$ μs; pulsed; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	-375	mV
R _{CEsat}	collector-emitter saturation resistance		-	45	75	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -4 A; I_B = -200 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	-1.1	V
		I_C = -5 A; I_B = -500 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	-1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -2 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-1	V
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -0.1 A; f = 100 MHz; T_{amb} = 25 °C	60	-	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	105	pF

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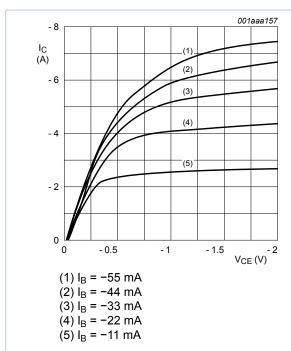


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

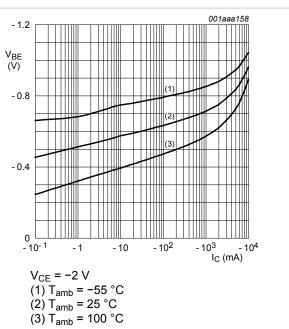


Fig. 6. Base-emitter voltage as a function of collector current; typical values

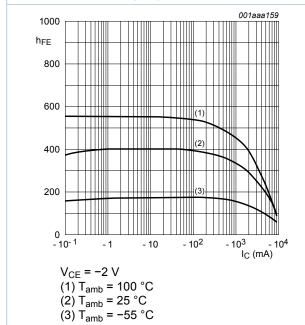


Fig. 7. DC current gain as a function of collector current; typical values

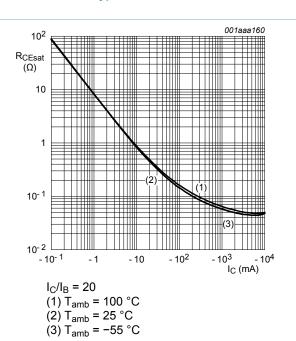


Fig. 8. Equivalent on-resistance as a function of collector current; typical values

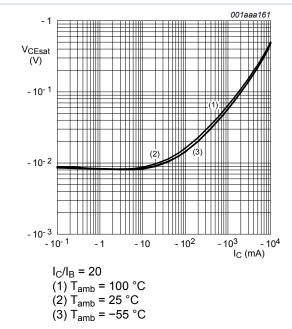


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

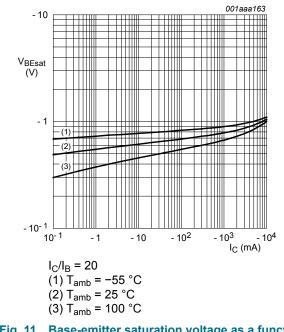


Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values

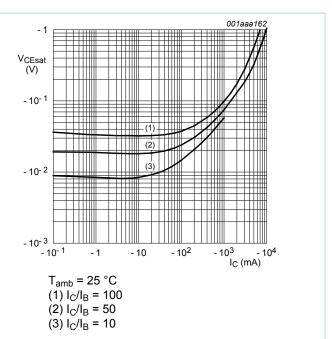


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

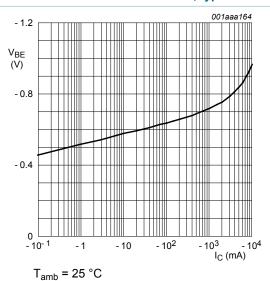


Fig. 12. Base-emitter voltage as a function of collector current; typical values

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11. Package outline

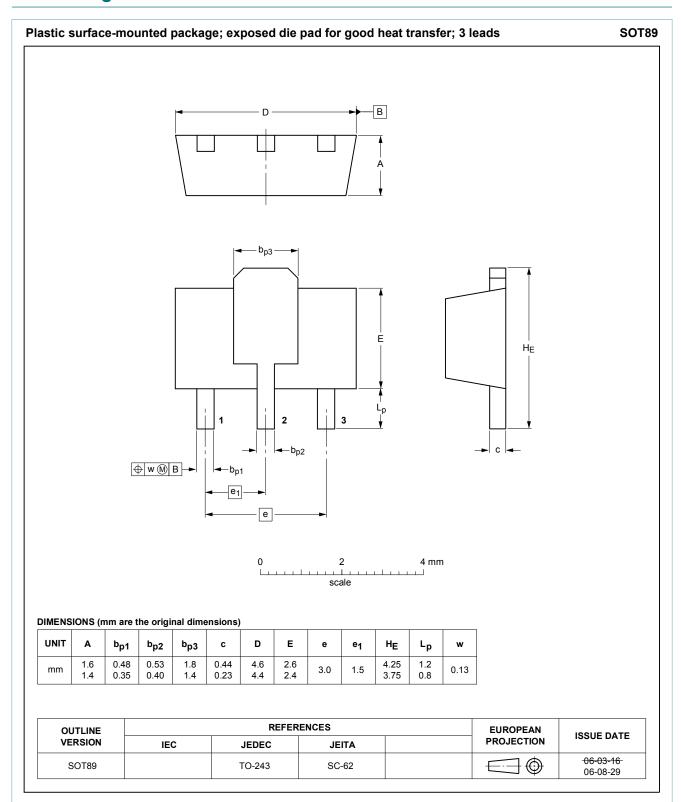
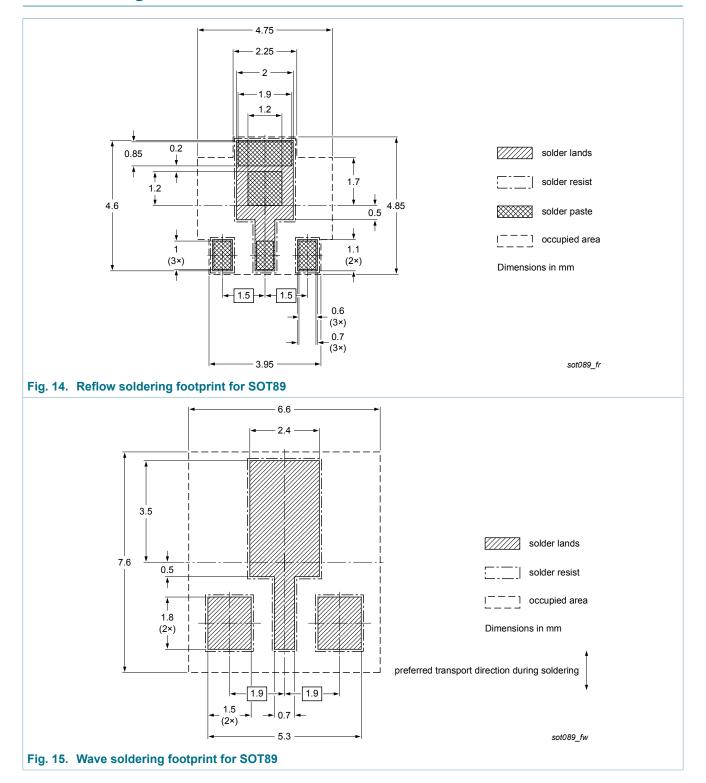


Fig. 13. Package outline SOT89

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12. Soldering



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13. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5540X v.3	20180320	Product data sheet	-	PBSS5540X v.2
Modifications:	Nexperia.	this data sheet has been redeave been adapted to the new content adapted		
PBSS5540X v.2	20041104	Product data sheet	-	PBSS5540X v.1
PBSS5540X v.1	20040115	Product data sheet	-	-

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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